

## N - CHANNEL ENHANCEMENT MODE

## FAST POWER MOS TRANSISTOR

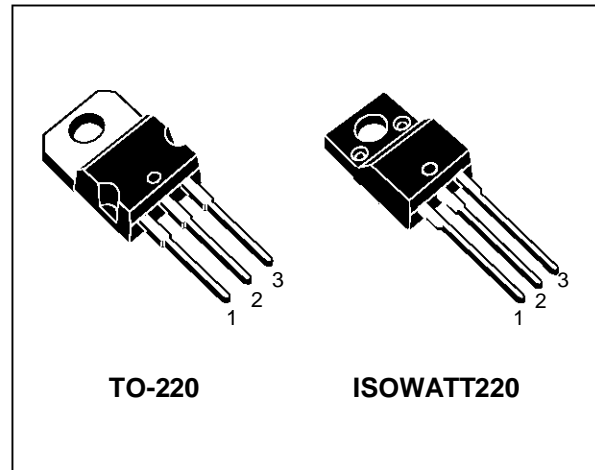
PRELIMINARY DATA

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STP3NA90	900 V	< 5.3 Ω	3 A
STP3NA90FI	900 V	< 5.3 Ω	1.9 A

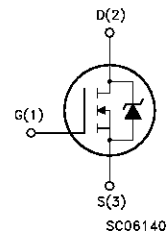
- TYPICAL R<sub>DS(on)</sub> = 4.4 Ω
- ± 30V GATE TO SOURCE VOLTAGE RATING
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW INTRINSIC CAPACITANCES
- GATE CHARGE MINIMIZED
- REDUCED THRESHOLD VOLTAGE SPREAD

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVE



### INTERNAL SCHEMATIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP3NA90	STP3NA90FI	
V <sub>DS</sub>	Drain-Source Voltage (V <sub>GS</sub> = 0)	900		V
V <sub>DGR</sub>	Drain-Gate Voltage (R <sub>GS</sub> = 20 KΩ)	900		V
V <sub>GS</sub>	Gate-Source Voltage	± 30		V
I <sub>D</sub>	Drain-Current (continuous) at T <sub>c</sub> = 25°C	3	1.9	A
I <sub>D</sub>	Drain-Current (continuous) at T <sub>c</sub> = 100°C	2	1.2	A
I <sub>DM</sub> (•)	Drain-Current (Pulsed)	12	12	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25°C	100	40	W
	Derating Factor	1.25	0.32	W/°C
V <sub>ISO</sub>	Insulation Withstand Voltage (DC)	-	2000	V
T <sub>stg</sub>	Storage Temperature	-65 to 150		°C
T <sub>j</sub>	Max Operating Junction Temperature	150		°C

(•) Pulse width limited by safe operating area

## THERMAL DATA

				TO220	ISOWATT220	
R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max		0.8	3.12	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max		62.5		°C/W
R <sub>thc-sink</sub>	Thermal Resistance Case-sink	Typ		0.5		°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose			300		°C

## AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max, $\delta < 1\%$ )	3	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	45	mJ
E <sub>AR</sub>	Repetitive Avalanche Energy (pulse width limited by T <sub>j</sub> max, $\delta < 1\%$ )	2	mJ
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (T <sub>c</sub> = 100 °C, pulse width limited by T <sub>j</sub> max, $\delta < 1\%$ )	2	A

ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

## OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 $\mu$ A V <sub>GS</sub> = 0	900			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating x 0.8 T <sub>c</sub> = 125 °C			250 1000	$\mu$ A $\mu$ A
I <sub>GSS</sub>	Gate-Source Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = $\pm 30$ V			$\pm 100$	mA

## ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 $\mu$ A	2.25	3	3.75	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10 V I <sub>D</sub> = 1.5 A V <sub>GS</sub> = 10 V I <sub>D</sub> = 1.5 A T <sub>c</sub> = 100 °C		4.4	5.3 10.6	$\Omega$ $\Omega$
I <sub>D(on)</sub>	On State Drain Current	V <sub>DS</sub> > I <sub>D(on)</sub> x R <sub>DS(on)</sub> max V <sub>GS</sub> = 10 V	3			A

## DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> x R <sub>DS(on)</sub> max I <sub>D</sub> = 1.5 A	1.5	2.8		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V f = 1 MHz V <sub>GS</sub> = 0		690	900	pF
C <sub>oss</sub>	Output Capacitance			80	105	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			20	30	pF

**ELECTRICAL CHARACTERISTICS** (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 450\text{ V}$		10	15	ns
$t_r$	Rise Time	$R_G = 4.7\ \Omega$ $I_D = 1.5\text{ A}$ $V_{GS} = 10\text{ V}$		10	15	ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 720\text{ V}$ $I_D = 3\text{ A}$ $R_G = 47\ \Omega$ $V_{GS} = 10\text{ V}$		360		A/ $\mu$ s
$Q_g$	Total Gate Charge	$V_{DD} = 720\text{ V}$ $I_D = 3\text{ A}$ $V_{GS} = 10\text{ V}$		35	50	nC
$Q_{gs}$	Gate-Source Charge			6		nC
$Q_{gd}$	Gate-Drain Charge			14		nC

**SWITCHING OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 720\text{ V}$ $I_D = 3\text{ A}$		11	10	ns
$t_f$	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		8	13	ns
$t_c$	Cross-over Time			19	26	ns

**SOURCE DRAIN DIODE**

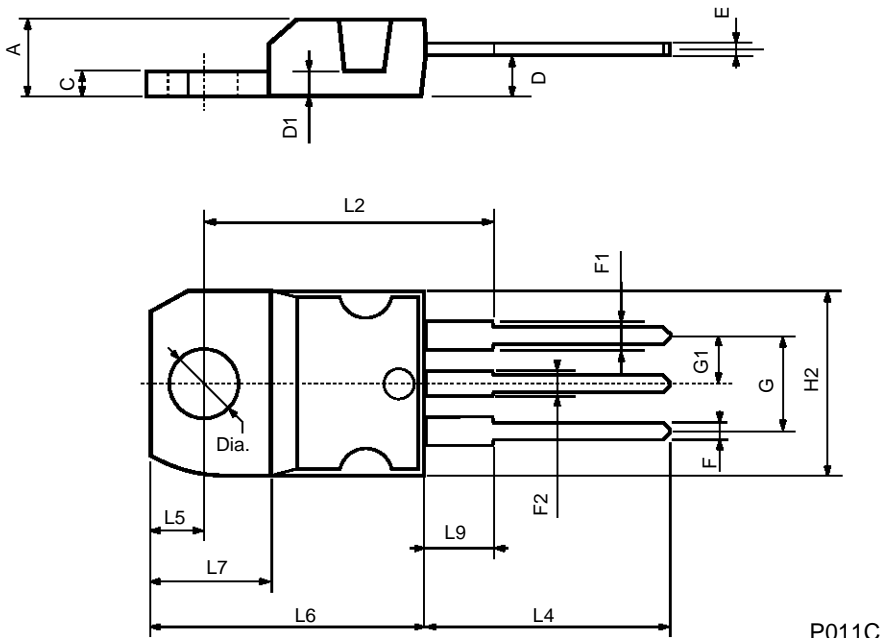
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				3	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				12	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 3\text{ A}$ $V_{GS} = 0$			1.6	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 3\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		950		ns
$Q_{rr}$	Reverse Recovery Charge			14.2		$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current			30		A

(\*) Pulsed: Pulse duration = 300  $\mu$ s, duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

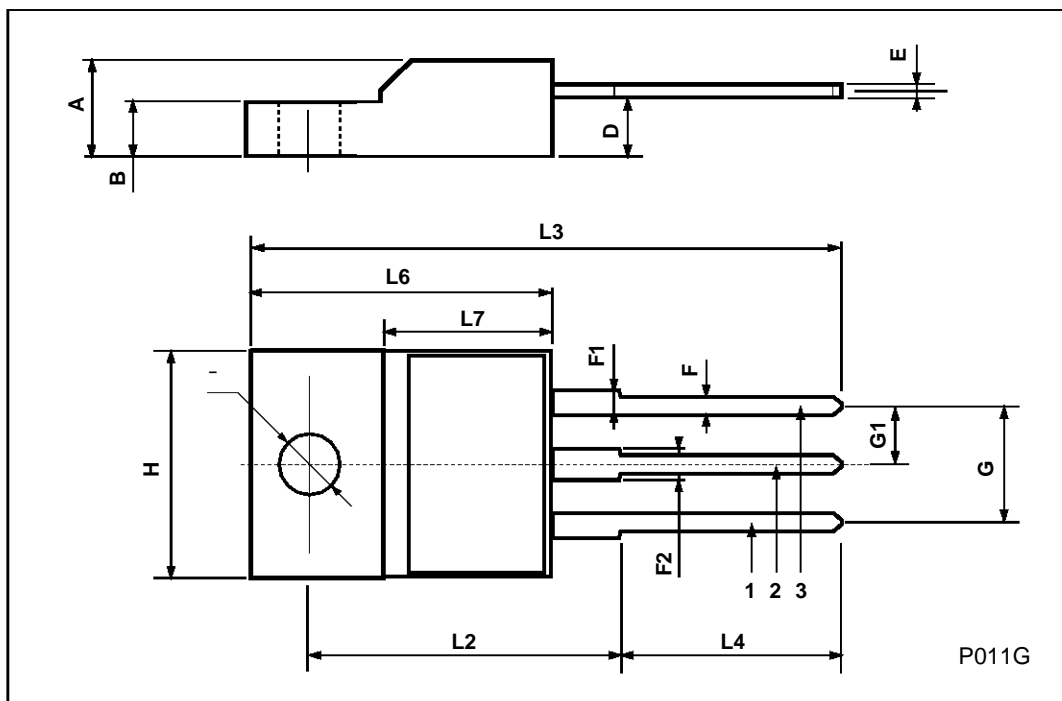
TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



## ISOWATT220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.4		0.7	0.015		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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